



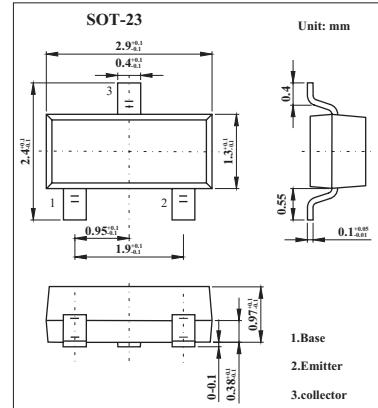
DONGGUAN NANJING ELECTRONICS LTD.,

Silicon NPN Epitaxial Type Transistor

2SC2712

■ Features

- High voltage and high current: $V_{CEO} = 50$ V, $I_C = 150$ mA (max)
- Excellent hFE linearity : h_{FE} ($I_C = 0.1$ mA)/ h_{FE} ($I_C = 2$ mA)= 0.95 (typ.)
- High hFE: $h_{FE} = 70 \sim 700$
- Low noise: NF = 1dB (typ.), 10dB (max)



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	150	mA
Base current	I_B	30	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 60$ V, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5$ V, $I_C = 0$			0.1	μA
DC current gain	h_{FE}	$V_{CE} = 6$ V, $I_C = 2$ mA	70		700	
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 100$ mA, $I_B = 10$ mA		0.1	0.25	V
Collector output capacitance	C_{ob}	$V_{CB} = 10$ V, $I_E = 0$, $f = 1$ MHz		2	3.5	pF
Noise figure	NF	$V_{CE} = 6$ V, $I_C = 0.1$ mA, $f = 1$ KHz, $R_g=10K\Omega$		1	10	dB
Transition frequency	f_T	$V_{CE} = 10$ V, $I_C = 1$ mA	80			MHz

■ hFE Classification

Marking	LO	LY	LG	LL
Rank	O	Y	GR	BL
hFE	70~140	120~240	200~400	350~700

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■ Typical Characteristics

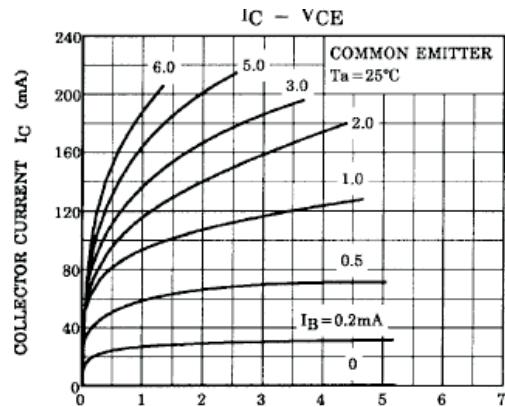


Fig.1 Collector Emitter Voltage

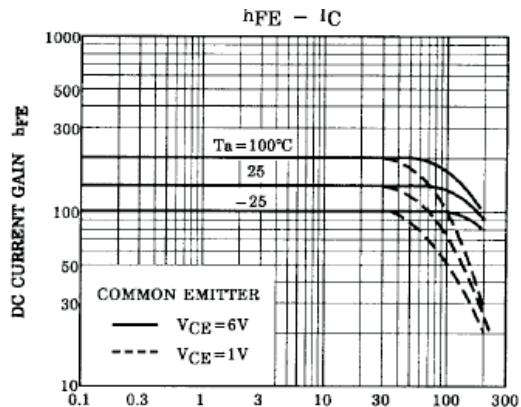


Fig.2 Collector Current

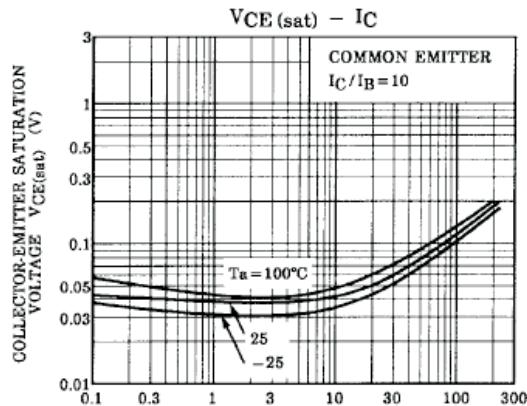


Fig.3 Collector Current

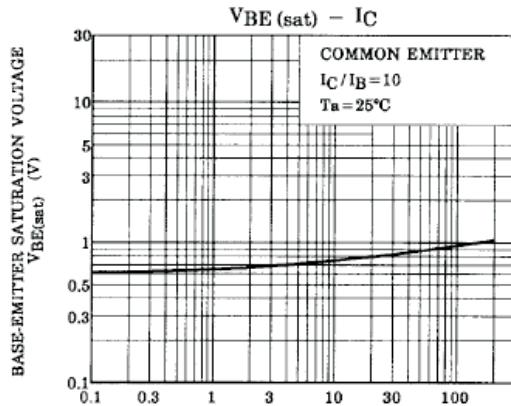


Fig.4 Collector Current

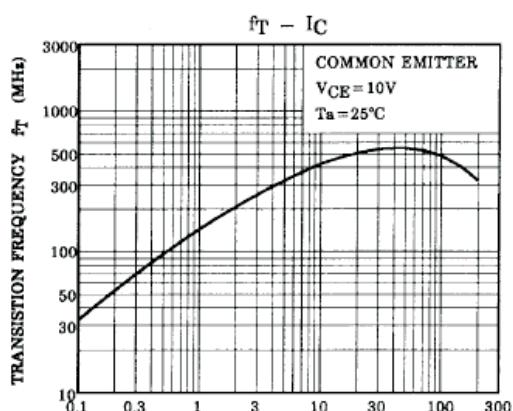


Fig.5 Collector Current

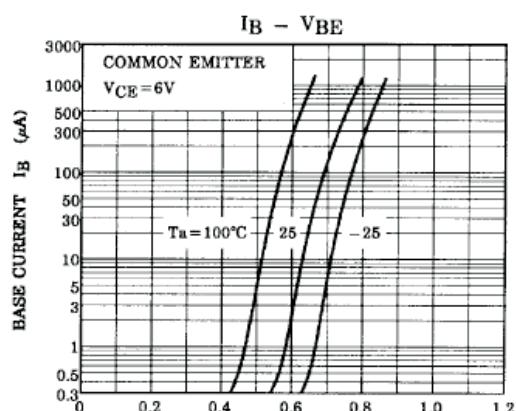


Fig.6 Base Emitter Voltage

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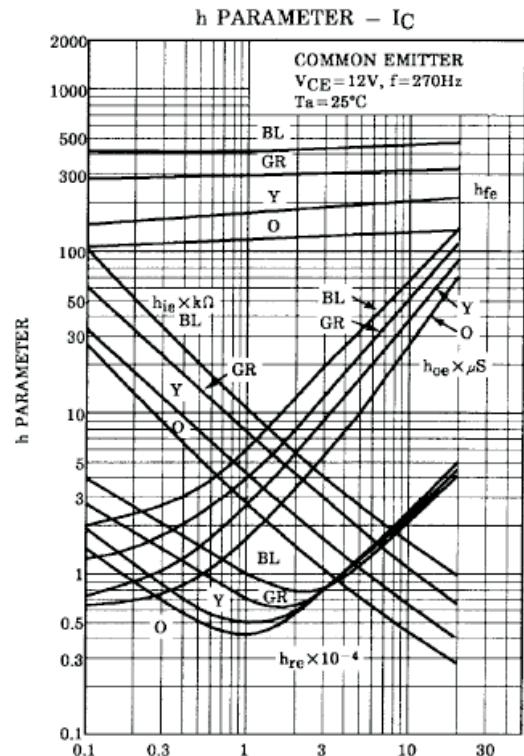


Fig.7 Collector Current

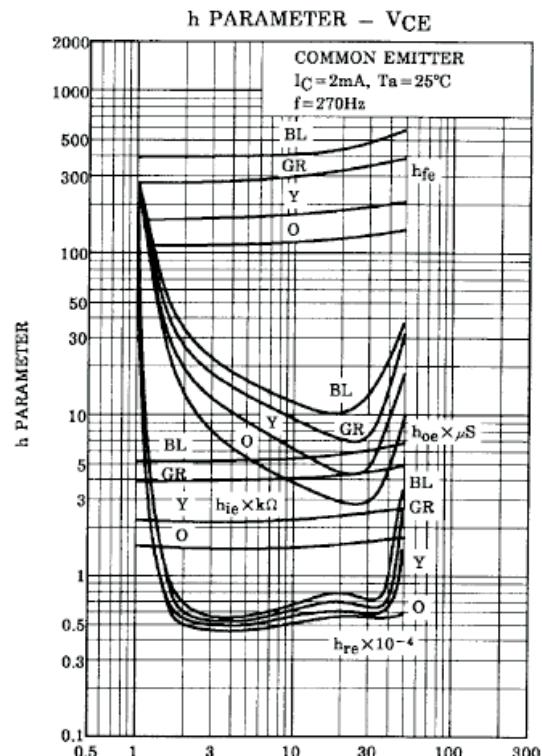


Fig.8 Collector Emitter Voltage

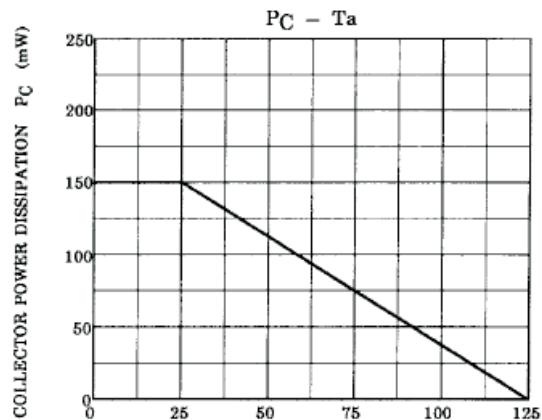


Fig.9 Ambient Temperature